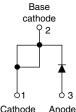


www.vishay.com

Vishay Semiconductors

Fast Soft Recovery Rectifier Diode, 20 A





TO-220AC FULL-PAK

	2
	•
01	03
Cathode	Anode

PRODUCT SUMMARY				
Package	TO-220FP			
I _{F(AV)}	20 A			
V_{R}	1000 V, 1200 V			
V _F at I _F	1.31 V			
I _{FSM}	320 A			
t _{rr}	95 ns			
T_J max.	150 °C			
Diode variation	Single die			
Snap factor	0.6			

FEATURES

- 150 °C max. operation junction temperature
- · Designed and qualified according to JEDEC-JESD47
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 approved
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912





RoHS **HALOGEN** FREE

APPLICATIONS

These devices are intended for use in output rectification and freewheeling in inverters, choppers and converters as well as in input rectification where severe restrictions on conducted EMI should be met.

DESCRIPTION

The VS-20ETF...FP... fast soft recovery rectifier series has been optimized for combined short reverse recovery time and low forward voltage drop.

The glass passivation ensures stable reliable operation in the most severe temperature and power cycling conditions.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	VALUES	UNITS				
V _{RRM}		1000 to 1200	V				
I _{F(AV)}	Sinusoidal waveform	20	^				
I _{FSM}		320	A				
t _{rr}	1 A, 100 A/µs	95	ns				
V _F	20 A, T _J = 25 °C	1.31	V				
T _J	Range	- 40 to 150	°C				

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} AT 150 °C mA		
VS-20ETF10FPPbF, VS-20ETF10FP-M3	1000	1100	6		
VS-20ETF12FPPbF, VS-20ETF12FP-M3	1200	1300	0		

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS VALUES			
Maximum average forward current	I _{F(AV)}	T _C = 50 °C, 180° conduction half sine wave	20		
Maximum peak one cycle	I	10 ms sine pulse, rated V _{RRM} applied	270	Α	
non-repetitive surge current	I _{FSM}	10 ms sine pulse, no voltage reapplied	320		
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rated V _{RRM} applied	365	A ² s	
Maximum i-t for fusing		10 ms sine pulse, no voltage reapplied	515	A-5	
Maximum I ² √t for fusing	I²√t	$I^2\sqrt{t}$ $t = 0.1$ ms to 10 ms, no voltage reapplied		A²√s	



Vishay Semiconductors

6

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	V_{FM}	20 A, T _J = 25 °C		1.31	V
Forward slope resistance	r _t	T _J = 150 °C		11.88	mΩ
Threshold voltage	V _{F(TO)}			0.93	V
Maximum reverse leakage current	Ірм	T _J = 25 °C	V _P = Bated V _{PPM}	0.1	mA

 $T_J = 150~^{\circ}C$

RECOVERY CHARACTERISTICS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	· •
Reverse recovery time	t _{rr}	I _F at 20 Apk	400	ns	I _{FM} t
Reverse recovery current	I _{rr}	25 A/μs	6.1	Α	$t_a \mid t_b$
Reverse recovery charge	Q _{rr}	25 °C	1.7	μC	dir/Q _{rr}
Snap factor	S	Typical	0.6		I I _{RM(REC)}

THERMAL - MECH	THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and sto temperature range	rage	T _J , T _{Stg}		- 40 to 150	°C
Maximum thermal resistan junction to case	ce,	R_{thJC}	DC operation	2.5	
Maximum thermal resistan junction to ambient	ce,	R_{thJA}		62	°C/W
Typical thermal resistance case to heatsink	,	R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque minimum maximum				6 (5)	kgf · cm
				12 (10)	(lbf · in)
Marking device			Case style TO-220 FULL-PAK		F10FP F12FP

35

www.vishay.com

Vishay Semiconductors

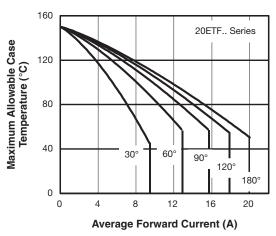


Fig. 1 - Current Rating Characteristics

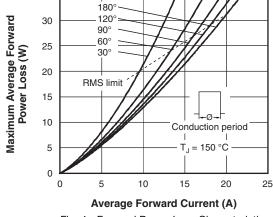


Fig. 4 - Forward Power Loss Characteristics

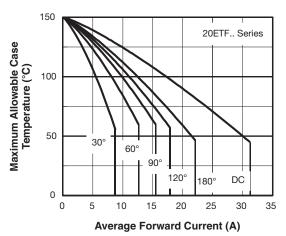


Fig. 2 - Current Rating Characteristics

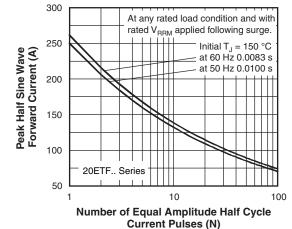


Fig. 5 - Maximum Non-Repetitive Surge Current

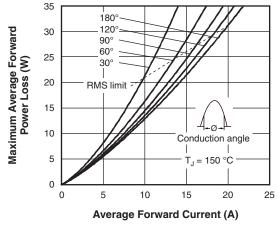


Fig. 3 - Forward Power Loss Characteristics

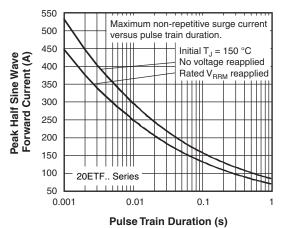


Fig. 6 - Maximum Non-Repetitive Surge Current

www.vishay.com

Vishay Semiconductors

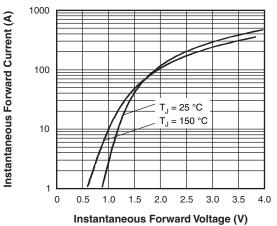
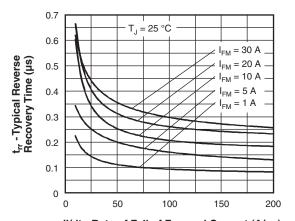


Fig. 7 - Forward Voltage Drop Characteristics



dl/dt - Rate of Fall of Forward Current (A/ μ s) Fig. 8 - Recovery Time Characteristics, T_J = 25 °C

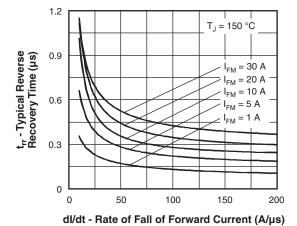
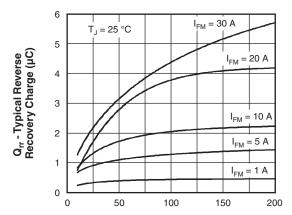
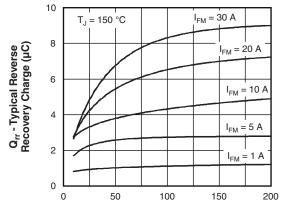


Fig. 9 - Recovery Time Characteristics, T_J = 150 °C



dl/dt - Rate of Fall of Forward Current (A/µs)

Fig. 10 - Recovery Charge Characteristics, T_J = 25 °C



dl/dt - Rate of Fall of Forward Current (A/µs)

Fig. 11 - Recovery Charge Characteristics, T_J = 150 °C



www.vishay.com

Vishay Semiconductors

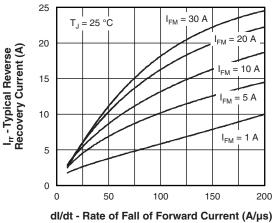
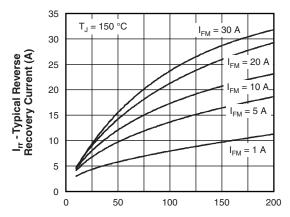


Fig. 12 - Recovery Current Characteristics, T_J = 25 °C



dl/dt - Rate of Fall of Forward Current (A/µs)

Fig. 13 - Recovery Current Characteristics, $T_J = 150 \, ^{\circ}\text{C}$

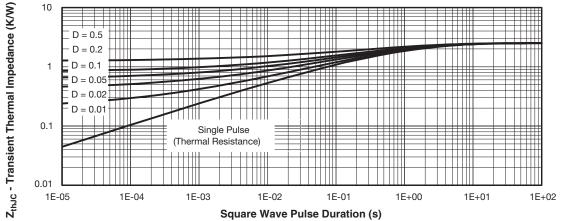
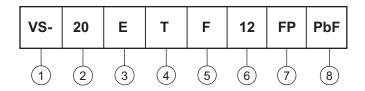


Fig. 14 - Thermal Impedance Z_{thJC} Characteristics

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (20 = 20 A)

3 - Circuit configuration:

E = Single diode

4 - Package:

5

T = TO-220

Type of silicon:

F = Fast soft recovery rectifier

6 - Voltage code x 100 = V_{RRM} - 10 = 1000 V 12 = 1200 V

7 - FULL-PAK

8 - Environmental digit:

• PbF = Lead (Pb)-free and RoHS compliant

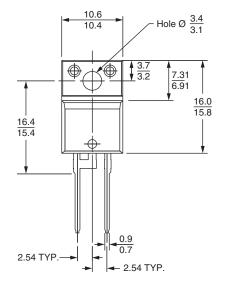
• -M3 = Halogen-free, RoHS compliant and terminations lead (Pb)-free

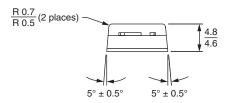
ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-20ETF10FPPbF	50	1000	Antistatic plastic tubes			
VS-20ETF10FP-M3	50	1000	Antistatic plastic tubes			
VS-20ETF12FPPbF	50	1000	Antistatic plastic tubes			
VS-20ETF12FP-M3	50	1000	Antistatic plastic tubes			

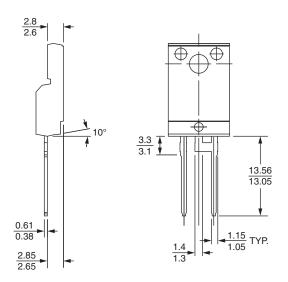
LINKS TO RELATED DOCUMENTS				
Dimensions		www.vishay.com/doc?95005		
Part marking information	TO-220 FP PbF	www.vishay.com/doc?95009		
Part marking information	TO-220 FP -M3	www.vishay.com/doc?95440		

Vishay Semiconductors

DIMENSIONS in millimeters







Lead assignments

<u>Diodes</u> 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000